

**Features**

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

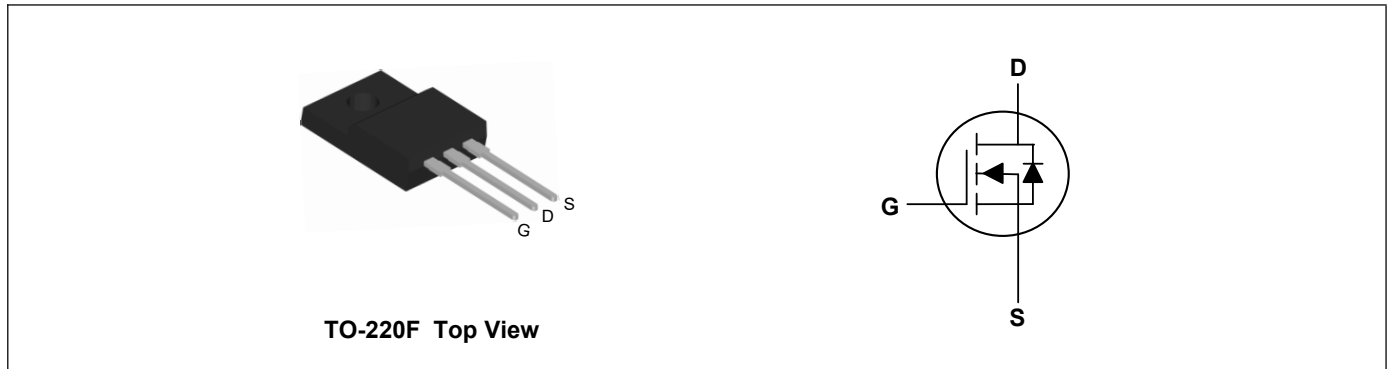
**Applications**

- High Frequency Point-of-Load, Synchronous Buck Converter
- Networking DC-DC Power System
- Load Switch

**Product Summary**



$V_{DS}$	80	V
$I_D$	60	A
$R_{DS(ON)}$ (at $V_{GS}=10V$ )	6	m $\Omega$



**Absolute Maximum Ratings( $T_C=25^{\circ}C$ , unless otherwise noted)**

Parameter	Symbol	Rating	Units
Drain-Source Voltage	$V_{DS}$	80	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current <sup>1</sup>	$I_D$	60	A
Pulsed Drain Current <sup>2</sup>	$I_{DM}$	240	A
Single Pulse Avalanche Energy <sup>3</sup>	$E_{AS}$	300	mJ
Total Power Dissipation	$P_D$	30	W
Storage Temperature Range	$T_{STG}$	-55 to 175	$^{\circ}C$
Operating Junction Temperature Range	$T_J$	-55 to 175	$^{\circ}C$

**Thermal Characteristics**

Parameter	Symbol	Typ	Max	Unit
Thermal Resistance Junction-Ambient <sup>1</sup>	$R_{\theta JA}$	---	60	$^{\circ}C/W$
Thermal Resistance Junction-Case <sup>1</sup>	$R_{\theta JC}$	---	5	$^{\circ}C/W$

**Electrical Characteristics ( $T_J=25^{\circ}\text{C}$ , unless otherwise noted)**

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	80	---	---	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=20A$	---	5.0	6.0	m $\Omega$
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	2.5	---	3.5	V
Drain-Source Leakage Current	$I_{DSS}$	$V_{DS}=80V, V_{GS}=0V, T_J=25^{\circ}\text{C}$	---	---	1	$\mu A$
Gate-Source Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	$\pm 100$	nA
Gate Resistance	$R_g$	$V_{DS}=0V, V_{GS}=0V, f=1\text{MHz}$	---	1.2	---	$\Omega$
Total Gate Charge	$Q_g$	$V_{DS}=40V, V_{GS}=10V, I_D=20A$	---	51	---	nC
Gate-Source Charge	$Q_{gs}$		---	15	---	
Gate-Drain Charge	$Q_{gd}$		---	13	---	
Turn-On Delay Time	$T_{d(on)}$	$V_{DD}=40V, V_{GS}=10V, I_D=20A$	---	16	---	ns
Rise Time	$T_r$		---	13	---	
Turn-Off Delay Time	$T_{d(off)}$		---	35	---	
Fall Time	$T_f$		---	13	---	
Input Capacitance	$C_{iss}$	$V_{DS}=40V, V_{GS}=0V, f=1\text{MHz}$	---	3325	---	pF
Output Capacitance	$C_{oss}$		---	470	---	
Reverse Transfer Capacitance	$C_{rss}$		---	22	---	

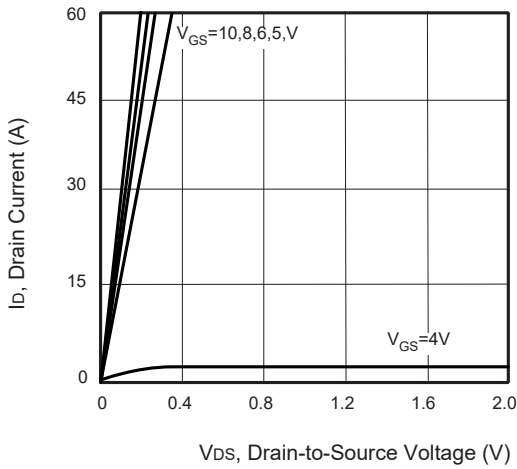
**Drain-Source Diode Characteristics**

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Diode Forward Voltage <sup>2</sup>	$V_{SD}$	$V_{GS}=0V, I_S=1A, T_J=25^{\circ}\text{C}$	---	0.7	---	V
Reverse Recovery Time	$t_{rr}$	$I_F=20A, V_{GS}=0V$ $di/dt=100A/\mu s, T_J=25^{\circ}\text{C}$	---	40	---	nS
Reverse Recovery Charge	$Q_{rr}$		---	100	---	nC

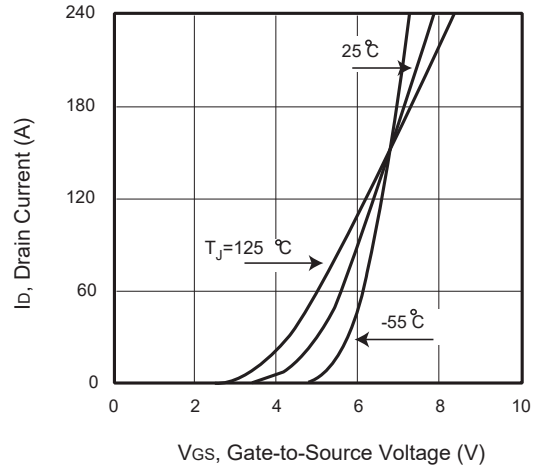
**Note:**

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width  $\leq 300\mu s$  , duty cycle  $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is  $V_{DD}=40V, V_{GS}=10V, L=0.5\text{mH}$

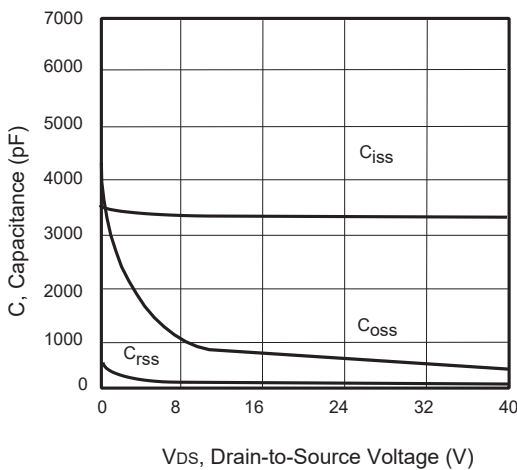
**Typical Characteristics**



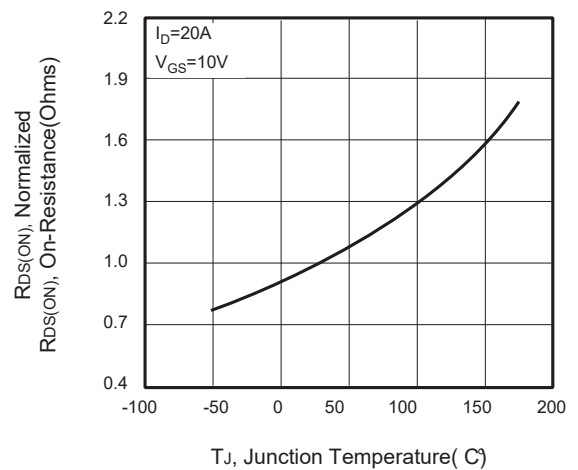
**Figure 1. Output Characteristics**



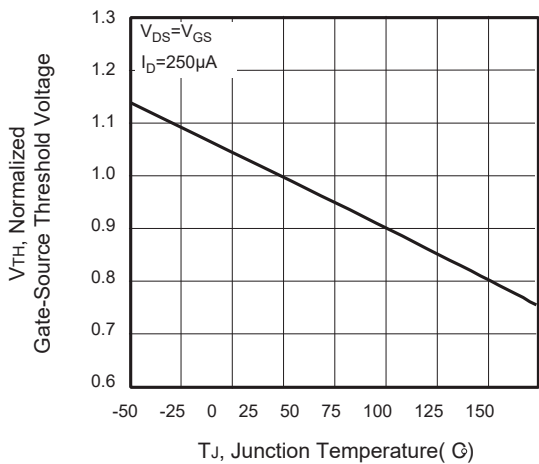
**Figure 2. Transfer Characteristics**



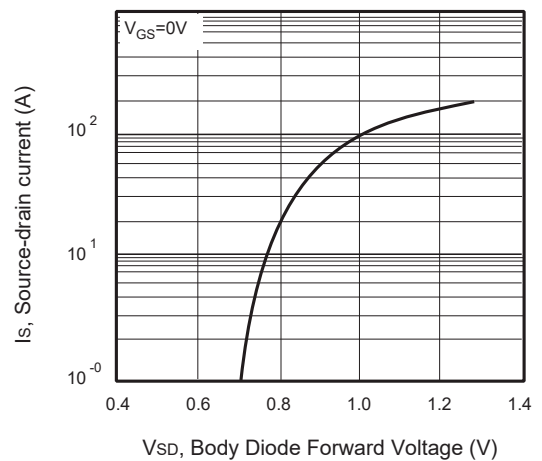
**Figure 3. Capacitance**



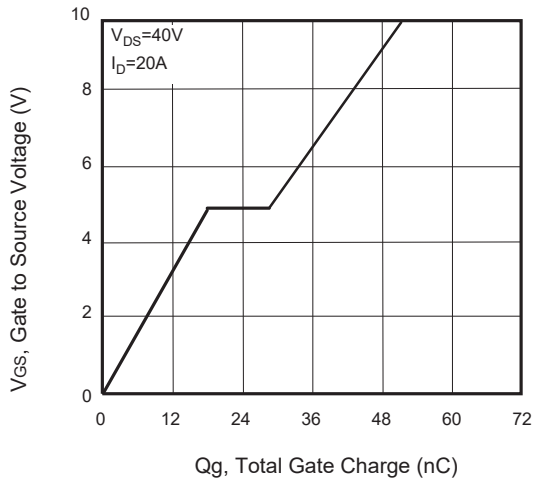
**Figure 4. On-Resistance Variation with Temperature**



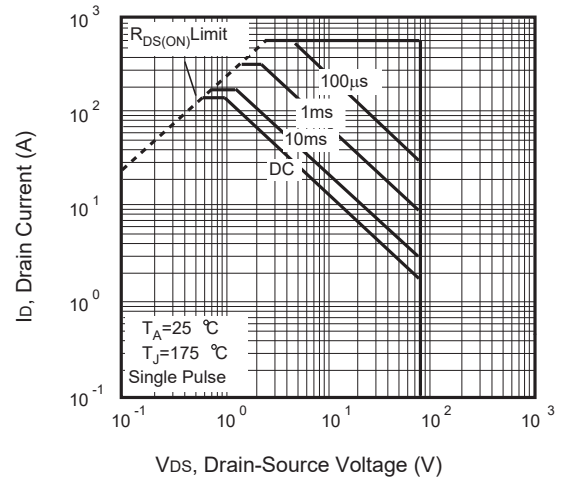
**Figure 5. Gate Threshold Variation with Temperature**



**Figure 6. Body Diode Forward Voltage Variation with Source Current**

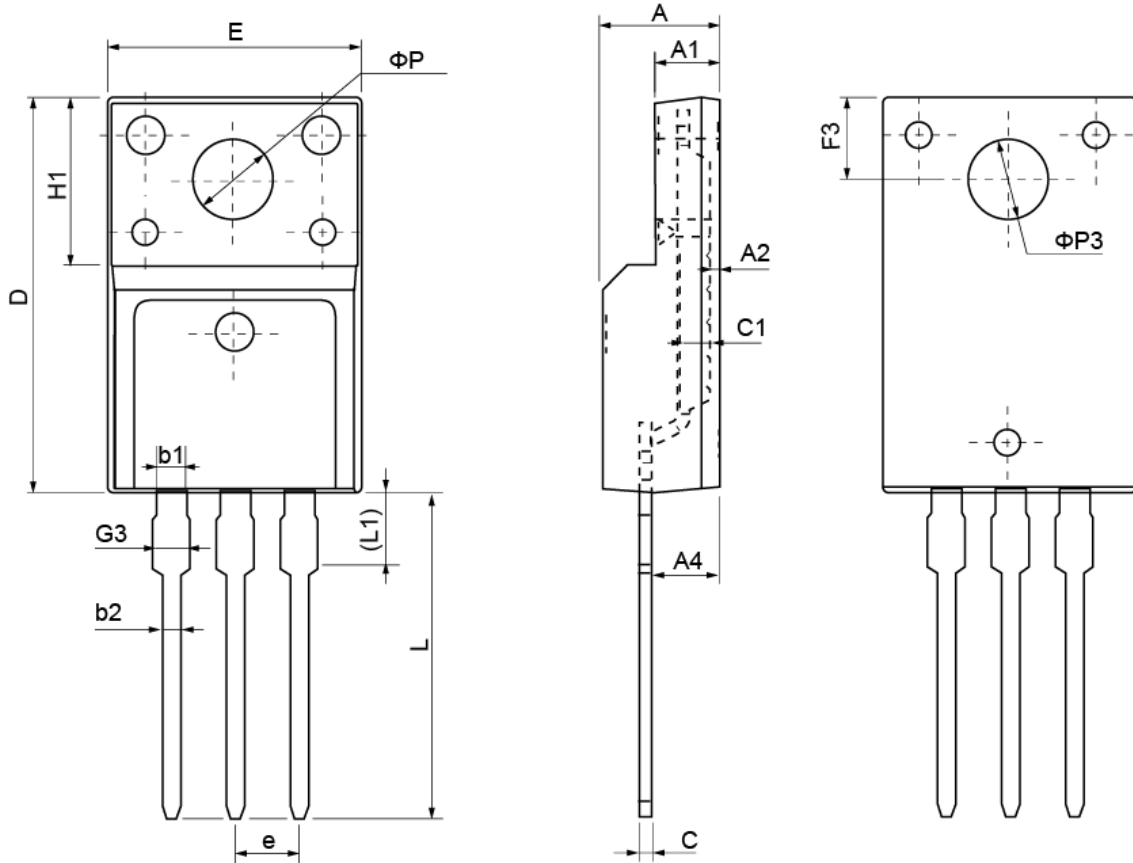


**Figure 7. Gate Charge**



**Figure 8. Maximum Safe Operating Area**

**TO-220F Package Outline Dimensions**



Symbol	Dimensions (unit:mm)			Symbol	Dimensions (unit:mm)		
	Min	Typ	Max		Min	Typ	Max
<b>A</b>	4.40	4.70	5.00	<b>H1</b>	6.70 REF		
<b>A1</b>	2.30	2.55	2.80	<b>L</b>	12.30	12.98	13.30
<b>A2</b>	0.30	0.50	0.70	<b>L1</b>	2.95	3.10	3.50
<b>A4</b>	2.45	2.80	3.05	<b>φ P</b>	3.03	3.20	3.50
<b>c</b>	0.30	0.50	0.70	<b>φ P3</b>	3.15	3.45	3.65
<b>c1</b>	1.20	1.30	1.40	<b>b1</b>	1.10	1.30	1.45
<b>D</b>	15.40	15.90	16.40	<b>b2</b>	0.60	0.80	1.00
<b>E</b>	9.86	10.16	10.46	<b>F3</b>	3.05	3.30	3.55
<b>e</b>	2.54 BSC			<b>G3</b>	1.15	1.35	1.55